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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I²C, IrDA, LINbus, QSPI, SAI, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, PWM, WDT
Number of I/O	38
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	160K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 10x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l451ccu6tr

3.4 Embedded Flash memory

STM32L451xx devices feature up to 512 Kbyte of embedded Flash memory available for storing programs and data in single bank architecture. The Flash memory contains 256 pages of 2 Kbyte.

Flexible protections can be configured thanks to option bytes:

- Readout protection (RDP) to protect the whole memory. Three levels are available:
  - Level 0: no readout protection
  - Level 1: memory readout protection: the Flash memory cannot be read from or written to if either debug features are connected, boot in RAM or bootloader is selected
  - Level 2: chip readout protection: debug features (Cortex-M4 JTAG and serial wire), boot in RAM and bootloader selection are disabled (JTAG fuse). This selection is irreversible.

Table 3. Access status versus readout protection level and execution modes

Area	Protection level	User execution			Debug, boot from RAM or boot from system memory (loader)		
		Read	Write	Erase	Read	Write	Erase
Main memory	1	Yes	Yes	Yes	No	No	No
	2	Yes	Yes	Yes	N/A	N/A	N/A
System memory	1	Yes	No	No	Yes	No	No
	2	Yes	No	No	N/A	N/A	N/A
Option bytes	1	Yes	Yes	Yes	Yes	Yes	Yes
	2	Yes	No	No	N/A	N/A	N/A
Backup registers	1	Yes	Yes	N/A(1)	No	No	N/A(1)
	2	Yes	Yes	N/A	N/A	N/A	N/A
SRAM2	1	Yes	Yes	Yes(1)	No	No	No(1)
	2	Yes	Yes	Yes	N/A	N/A	N/A

1. Erased when RDP change from Level 1 to Level 0.

- Write protection (WRP): the protected area is protected against erasing and programming. Two areas can be selected, with 2-Kbyte granularity.
- Proprietary code readout protection (PCROP): a part of the flash memory can be protected against read and write from third parties. The protected area is execute-only: it can only be reached by the STM32 CPU, as an instruction code, while all other accesses (DMA, debug and CPU data read, write and erase) are strictly prohibited. The PCROP area granularity is 64-bit wide. An additional option bit (PCROP_RDP) allows to select if the PCROP area is erased or not when the RDP protection is changed from Level 1 to Level 0.

3.11 Clocks and startup

The clock controller (see *Figure 4*) distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low-power modes and ensures clock robustness. It features:

- **Clock prescaler:** to get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler
- **Safe clock switching:** clock sources can be changed safely on the fly in run mode through a configuration register.
- **Clock management:** to reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.
- **System clock source:** four different clock sources can be used to drive the master clock SYSCLK:
  - 4-48 MHz high-speed external crystal or ceramic resonator (HSE), that can supply a PLL. The HSE can also be configured in bypass mode for an external clock.
  - 16 MHz high-speed internal RC oscillator (HSI16), trimmable by software, that can supply a PLL
  - Multispeed internal RC oscillator (MSI), trimmable by software, able to generate 12 frequencies from 100 kHz to 48 MHz. When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be automatically trimmed by hardware to reach better than ±0.25% accuracy. The MSI can supply a PLL.
  - System PLL which can be fed by HSE, HSI16 or MSI, with a maximum frequency at 80 MHz.
- **RC48 with clock recovery system (HSI48)**: internal RC48 MHz clock source can be used to drive the SDMMC or the RNG peripherals. This clock can be output on the MCO.
- **Auxiliary clock source:** two ultralow-power clock sources that can be used to drive the real-time clock:
  - 32.768 kHz low-speed external crystal (LSE), supporting four drive capability modes. The LSE can also be configured in bypass mode for an external clock.
  - 32 kHz low-speed internal RC (LSI), also used to drive the independent watchdog. The LSI clock accuracy is ±5% accuracy.
- **Peripheral clock sources:** Several peripherals (SDMMC, RNG, SAI, USARTs, I2Cs, LPTimers, ADC) have their own independent clock whatever the system clock. Two PLLs, each having three independent outputs allowing the highest flexibility, can generate independent clocks for the ADC, the SDMMC/RNG and the SAI.
- **Startup clock:** after reset, the microcontroller restarts by default with an internal 4 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.
- **Clock security system (CSS):** this feature can be enabled by software. If a HSE clock failure occurs, the master clock is automatically switched to HSI16 and a software

The main features of the touch sensing controller are the following:

- Proven and robust surface charge transfer acquisition principle
- Supports up to 21 capacitive sensing channels
- Up to 3 capacitive sensing channels can be acquired in parallel offering a very good response time
- Spread spectrum feature to improve system robustness in noisy environments
- Full hardware management of the charge transfer acquisition sequence
- Programmable charge transfer frequency
- Programmable sampling capacitor I/O pin
- Programmable channel I/O pin
- Programmable max count value to avoid long acquisition when a channel is faulty
- Dedicated end of acquisition and max count error flags with interrupt capability
- One sampling capacitor for up to 3 capacitive sensing channels to reduce the system components
- Compatible with proximity, touchkey, linear and rotary touch sensor implementation
- Designed to operate with STMTouch touch sensing firmware library

Note: The number of capacitive sensing channels is dependent on the size of the packages and subject to I/O availability.

3.21 Digital filter for Sigma-Delta Modulators (DFSDM)

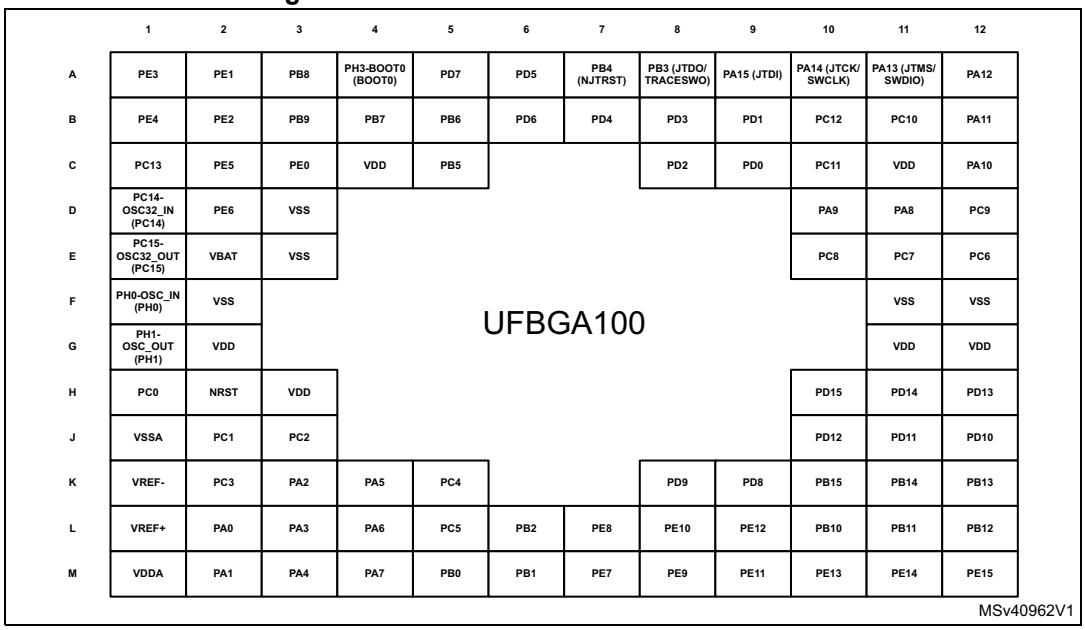
The device embeds one DFSDM with 2 digital filters modules and 4 external input serial channels (transceivers) or alternately 4 internal parallel inputs support.

The DFSDM peripheral is dedicated to interface the external ΣΔ modulators to microcontroller and then to perform digital filtering of the received data streams (which represent analog value on ΣΔ modulators inputs). DFSDM can also interface PDM (Pulse Density Modulation) microphones and perform PDM to PCM conversion and filtering in

The Quad SPI interface supports:

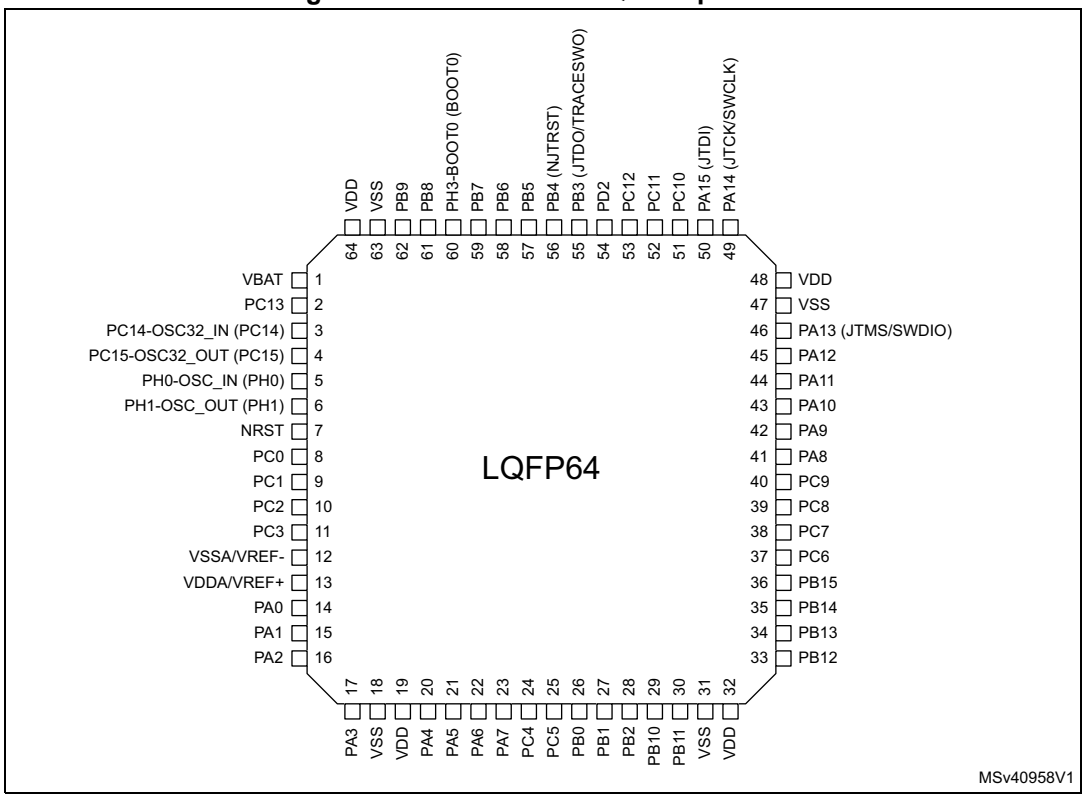
- Three functional modes: indirect, status-polling, and memory-mapped
- Dual-flash mode, where 8 bits can be sent/received simultaneously by accessing two flash memories in parallel.
- SDR and DDR support
- Fully programmable opcode for both indirect and memory mapped mode
- Fully programmable frame format for both indirect and memory mapped mode
- Each of the 5 following phases can be configured independently (enable, length, single/dual/quad communication)
  - Instruction phase
  - Address phase
  - Alternate bytes phase
  - Dummy cycles phase
  - Data phase
- Integrated FIFO for reception and transmission
- 8, 16, and 32-bit data accesses are allowed
- DMA channel for indirect mode operations
- Programmable masking for external flash flag management
- Timeout management
- Interrupt generation on FIFO threshold, timeout, status match, operation complete, and access error

Figure 7. STM32L451Vx UFBGA100 ballout(1)



1. The above figure shows the package top view.

Figure 8. STM32L451Rx LQFP64 pinout(1)



1. The above figure shows the package top view.

Table 16. STM32L451xx pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
UFQFPN48	WLCSP64	LQFP64	UFBGA64	LQFP100	UFBGA100					Alternate functions	Additional functions
45	A6	61	B3	95	A3	PB8	I/O	FT_f	-	I2C1_SCL, CAN1_RX, SDMMC1_D4, SAI1_MCLK_A, TIM16_CH1, EVENTOUT	-
46	C6	62	A3	96	B3	PB9	I/O	FT_f	-	IR_OUT, I2C1_SDA, SPI2_NSS, CAN1_TX, SDMMC1_D5, SAI1_FS_A, EVENTOUT	-
-	-	-	-	97	C3	PE0	I/O	FT	-	TIM16_CH1, EVENTOUT	-
-	-	-	-	98	A2	PE1	I/O	FT	-	EVENTOUT	-
47	A7	63	D4	99	D3	VSS	S	-	-	-	-
48	A8	64	E4	100	C4	VDD	S	-	-	-	-

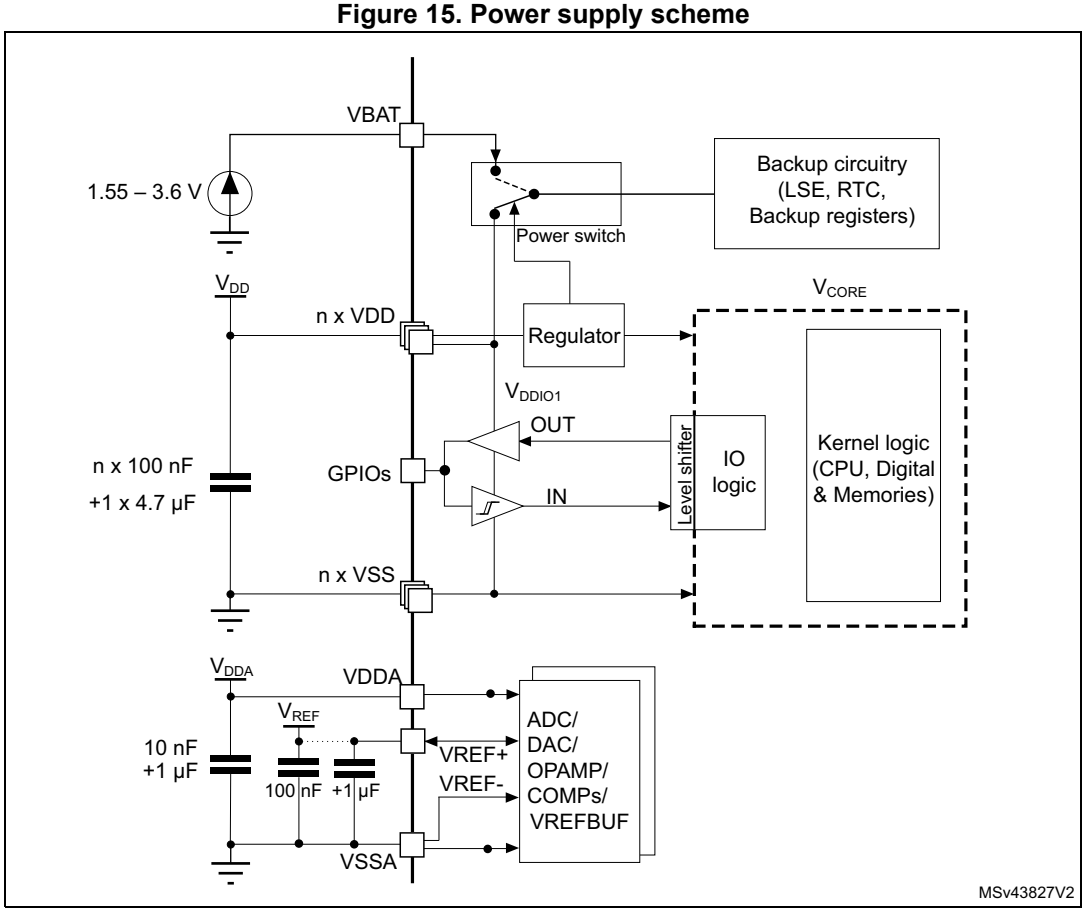
1. PC13, PC14 and PC15 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is limited:
   - The speed should not exceed 2 MHz with a maximum load of 30 pF
   - These GPIOs must not be used as current sources (e.g. to drive an LED).
2. After a Backup domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the RTC registers which are not reset by the system reset. For details on how to manage these GPIOs, refer to the Backup domain and RTC register descriptions in the RM0394 reference manual.
3. After reset, these pins are configured as JTAG/SW debug alternate functions, and the internal pull-up on PA15, PA13, PB4 pins and the internal pull-down on PA14 pin are activated.

Table 18. Alternate function AF8 to AF15[1] (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4/ LPUART1/ CAN1	CAN1/TSC	CAN1/ QUADSPI	-	SDMMC1/ COMP1/ COMP2	SAI1	TIM2/TIM15/ TIM16/LPTIM2	EVENTOUT
Port B	PB0	-	-	QUADSPI_ BK1_IO1	-	COMP1_OUT	SAI1_EXTCLK	-	EVENTOUT
	PB1	LPUART1_RTS _DE	-	QUADSPI_ BK1_IO0	-	-	-	LPTIM2_IN1	EVENTOUT
	PB2	-	-	-	-	-	-	-	EVENTOUT
	PB3	-	-	-	-	-	SAI1_SCK_B	-	EVENTOUT
	PB4	-	TSC_G2_IO1	-	-	-	SAI1_MCLK_B	-	EVENTOUT
	PB5	-	TSC_G2_IO2	-	-	COMP2_OUT	SAI1_SD_B	TIM16_BKIN	EVENTOUT
	PB6	CAN1_TX	TSC_G2_IO3	-	-	-	SAI1_FS_B	TIM16_CH1N	EVENTOUT
	PB7	UART4_CTS	TSC_G2_IO4	-	-	-	-	-	EVENTOUT
	PB8	-	CAN1_RX	-	-	SDMMC1_D4	SAI1_MCLK_A	TIM16_CH1	EVENTOUT
	PB9	-	CAN1_TX	-	-	SDMMC1_D5	SAI1_FS_A	-	EVENTOUT
	PB10	LPUART1_RX	TSC_SYNC	QUADSPI_CLK	-	COMP1_OUT	SAI1_SCK_A	-	EVENTOUT
	PB11	LPUART1_TX	-	QUADSPI_ BK1_NCS	-	COMP2_OUT	-	-	EVENTOUT
	PB12	LPUART1_RTS _DE	TSC_G1_IO1	CAN1_RX	-	-	SAI1_FS_A	TIM15_BKIN	EVENTOUT
	PB13	LPUART1_CTS	TSC_G1_IO2	CAN1_TX	-	-	SAI1_SCK_A	TIM15_CH1N	EVENTOUT
	PB14	-	TSC_G1_IO3	-	-	-	SAI1_MCLK_A	TIM15_CH1	EVENTOUT
	PB15	-	TSC_G1_IO4	-	-	-	SAI1_SD_A	TIM15_CH2	EVENTOUT

6.1.6 Power supply scheme

Figure 15. Power supply scheme



Caution: Each power supply pair (V_{DD}/V_{SS}, V_{DDA}/V_{SSA} etc.) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

6.3.4 Embedded voltage reference

The parameters given in *Table 26* are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*.

Table 26. Embedded internal voltage reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	–40 °C < T_A < +130 °C	1.182	1.212	1.232	V
$t_{S\_vrefint}$ (1)	ADC sampling time when reading the internal reference voltage	-	4(2)	-	-	µs
$t_{start\_vrefint}$	Start time of reference voltage buffer when ADC is enable	-	-	8	12(2)	µs
$I_{DD}(V_{REFINTBUF})$	V_{REFINT} buffer consumption from V_{DD} when converted by ADC	-	-	12.5	20(2)	µA
ΔV_{REFINT}	Internal reference voltage spread over the temperature range	V_{DD} = 3 V	-	5	7.5(2)	mV
T_{Coeff}	Temperature coefficient	–40°C < T_A < +130°C	-	30	50(2)	ppm/°C
A_{Coeff}	Long term stability	1000 hours, T = 25°C	-	300	1000(2)	ppm
$V_{DDCoeff}$	Voltage coefficient	3.0 V < V_{DD} < 3.6 V	-	250	1200(2)	ppm/V
V_{REFINT_DIV1}	1/4 reference voltage	-	24	25	26	% V_{REFINT}
V_{REFINT_DIV2}	1/2 reference voltage		49	50	51	
V_{REFINT_DIV3}	3/4 reference voltage		74	75	76	

1. The shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design.

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 61: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see *Table 41: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the I/O supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DDIOx} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DDIOx} is the I/O supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_S$

C_S is the PCB board capacitance including the pad pin.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 41*. The MCU is placed under the following conditions:

- All I/O pins are in Analog mode
- The given value is calculated by measuring the difference of the current consumptions:
  - when the peripheral is clocked on
  - when the peripheral is clocked off
- Ambient operating temperature and supply voltage conditions summarized in *Table 20: Voltage characteristics*
- The power consumption of the digital part of the on-chip peripherals is given in *Table 41*. The power consumption of the analog part of the peripherals (where applicable) is indicated in each related section of the datasheet.

Table 41. Peripheral current consumption

Peripheral		Range 1	Range 2	Low-power run and sleep	Unit
AHB	Bus Matrix(1)	3.2	2.9	3.1	µA/MHz
	ADC independent clock domain	0.4	0.1	0.2	
	ADC clock domain	2.1	1.9	1.9	
	CRC	0.4	0.2	0.3	
	DMA1	1.4	1.3	1.4	
	DMA2	1.5	1.3	1.4	
	FLASH	6.2	5.2	5.8	
	GPIOA(2)	1.7	1.4	1.6	
	GPIOB(2))	1.6	1.3	1.6	
	GPIOC(2)	1.7	1.5	1.6	
	GPIOD(2)	1.8	1.6	1.7	
	GPIOE(2)	1.7	1.6	1.6	
	GPIOH(2)	0.6	0.6	0.5	
	QSPI	7.0	5.8	7.3	
	RNG independent clock domain	2.2	N/A	N/A	
	RNG clock domain	0.5	N/A	N/A	
	SRAM1	0.8	0.9	0.7	
	SRAM2	1.0	0.8	0.8	
	TSC	1.6	1.3	1.3	
	All AHB Peripherals	25.2	21.7	23.6	
APB1	AHB to APB1 bridge(3)	0.9	0.7	0.9	
	CAN1	4.1	3.2	3.9	
	DAC1	2.4	1.8	2.2	

Table 41. Peripheral current consumption (continued)

Peripheral		Range 1	Range 2	Low-power run and sleep	Unit
APB1	RTCA	1.7	1.1	2.1	µA/MHz
	CRS	0.3	0.3	0.6	
	I2C1 independent clock domain	3.5	2.8	3.4	
	I2C1 clock domain	1.1	0.9	1.0	
	I2C2 independent clock domain	3.5	3.0	3.4	
	I2C2 clock domain	1.1	0.7	0.9	
	I2C3 independent clock domain	2.9	2.3	2.5	
	I2C3 clock domain	0.9	0.4	0.8	
	LPUART1 independent clock domain	1.9	1.6	1.8	
	LPUART1 clock domain	0.6	0.6	0.6	
	LPTIM1 independent clock domain	2.9	2.4	2.8	
	LPTIM1 clock domain	0.8	0.4	0.7	
	LPTIM2 independent clock domain	3.1	2.7	3.9	
	LPTIM2 clock domain	0.8	0.7	0.8	
	OPAMP	0.4	0.2	0.4	
	PWR	0.4	0.1	0.4	
	SPI2	1.8	1.6	1.6	
	SPI3	1.7	1.3	1.6	
	TIM2	6.2	5.0	5.9	
	TIM6	1.0	0.6	0.9	
	USART2 independent clock domain	4.1	3.6	3.8	
	USART2 clock domain	1.3	0.9	1.1	
	USART3 independent clock domain	4.3	3.5	4.2	
	USART3 clock domain	1.5	1.1	1.3	
	WWDG	0.5	0.5	0.5	
	All APB1 on	51.5	35.5	48.6	

6.3.7 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.

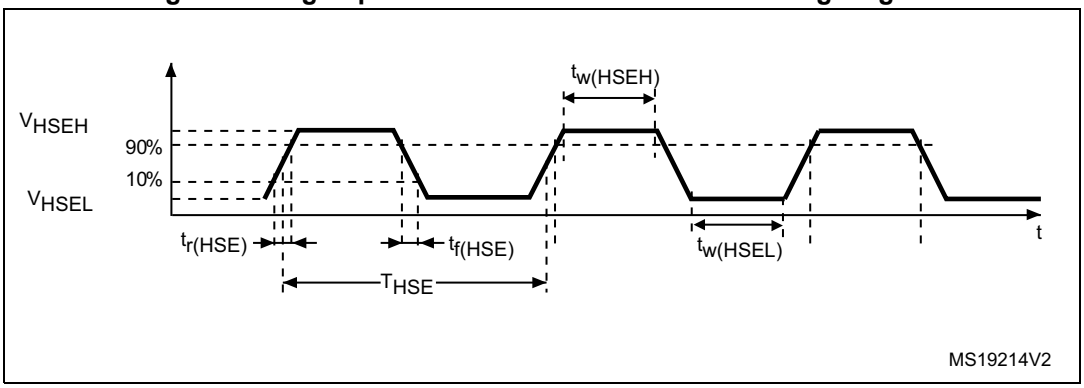
The external clock signal has to respect the I/O characteristics in *Section 6.3.14*. However, the recommended clock input waveform is shown in *Figure 18: High-speed external clock source AC timing diagram*.

Table 45. High-speed external user clock characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency	Voltage scaling Range 1	-	8	48	MHz
		Voltage scaling Range 2	-	8	26	
V_{HSEH}	OSC_IN input pin high level voltage	-	0.7 V_{DDIOx}	-	V_{DDIOx}	V
V_{HSEL}	OSC_IN input pin low level voltage	-	V_{SS}	-	0.3 V_{DDIOx}	
$t_{w(HSEH)}$ $t_{w(HSEL)}$	OSC_IN high or low time	Voltage scaling Range 1	7	-	-	ns
		Voltage scaling Range 2	18	-	-	

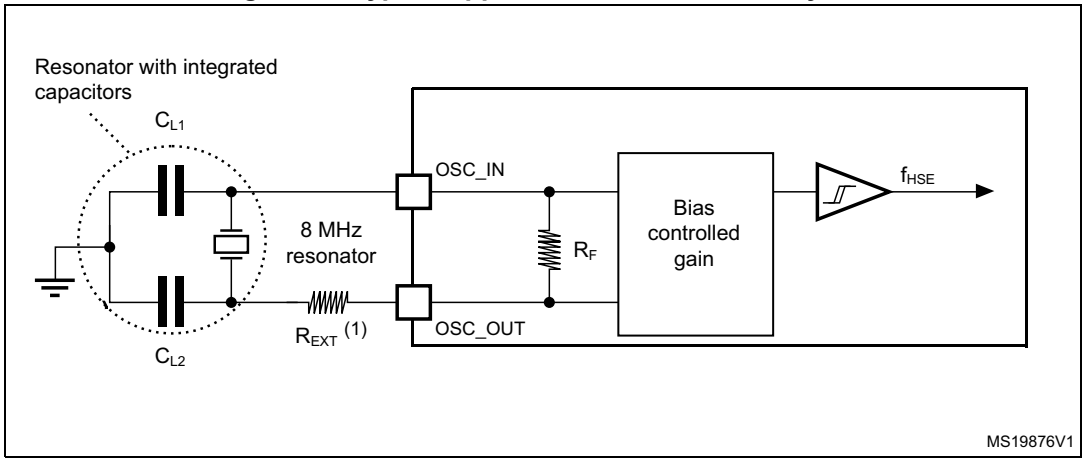
1. Guaranteed by design.

Figure 18. High-speed external clock source AC timing diagram



Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 20. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 48*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 48. LSE oscillator characteristics (f_{LSE} = 32.768 kHz)(1)

Symbol	Parameter	Conditions(2)	Min	Typ	Max	Unit
$I_{DD(LSE)}$	LSE current consumption	LSEDRV[1:0] = 00 Low drive capability	-	250	-	nA
		LSEDRV[1:0] = 01 Medium low drive capability	-	315	-	
		LSEDRV[1:0] = 10 Medium high drive capability	-	500	-	
		LSEDRV[1:0] = 11 High drive capability	-	630	-	
$Gm_{critmax}$	Maximum critical crystal gm	LSEDRV[1:0] = 00 Low drive capability	-	-	0.5	µA/V
		LSEDRV[1:0] = 01 Medium low drive capability	-	-	0.75	
		LSEDRV[1:0] = 10 Medium high drive capability	-	-	1.7	
		LSEDRV[1:0] = 11 High drive capability	-	-	2.7	
$t_{SU(LSE)}$(3)	Startup time	V_{DD} is stabilized	-	2	-	s

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 57. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]	Unit
				8 MHz/ 80 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 MHz to 30 MHz	-8	dBµV
			30 MHz to 130 MHz	2	
			130 MHz to 1 GHz	5	
			1 GHz to 2 GHz	8	
			EMI Level	2.5	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

Table 58. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to ANSI/ESDA/JEDEC JS-001	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1	C3	250	

1. Guaranteed by characterization results.

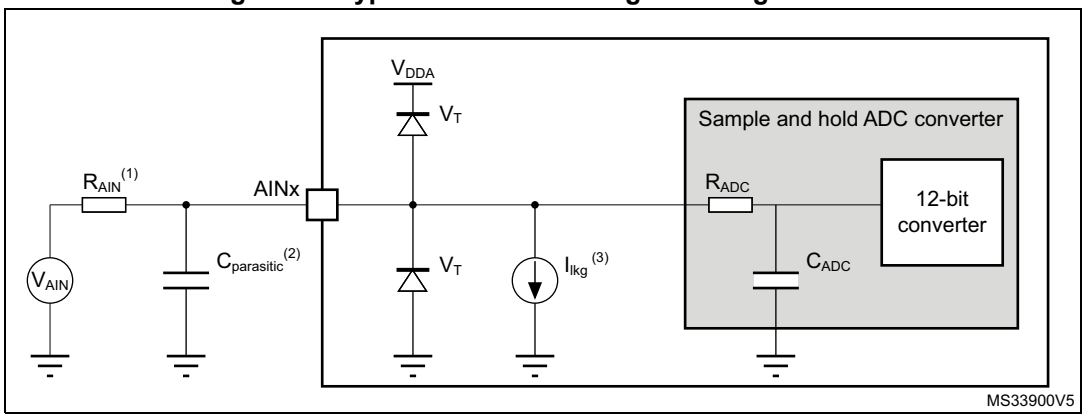
Table 69. ADC accuracy - limited test conditions 1(1)(2)(3)

Sym-bol	Parameter	Conditions(4)			Min	Typ	Max	Unit
ET	Total unadjusted error	ADC clock frequency ≤ 80 MHz, Sampling rate ≤ 5.33 Msps, V_{DDA} = VREF+ = 3 V, TA = 25 °C	Single ended	Fast channel (max speed)	-	4	5	LSB
				Slow channel (max speed)	-	4	5	
			Differential	Fast channel (max speed)	-	3.5	4.5	
				Slow channel (max speed)	-	3.5	4.5	
EO	Offset error		Single ended	Fast channel (max speed)	-	1	2.5	
				Slow channel (max speed)	-	1	2.5	
			Differential	Fast channel (max speed)	-	1.5	2.5	
				Slow channel (max speed)	-	1.5	2.5	
EG	Gain error		Single ended	Fast channel (max speed)	-	2.5	4.5	
				Slow channel (max speed)	-	2.5	4.5	
			Differential	Fast channel (max speed)	-	2.5	3.5	
				Slow channel (max speed)	-	2.5	3.5	
ED	Differential linearity error		Single ended	Fast channel (max speed)	-	1	1.5	
				Slow channel (max speed)	-	1	1.5	
			Differential	Fast channel (max speed)	-	1	1.2	
				Slow channel (max speed)	-	1	1.2	
EL	Integral linearity error		Single ended	Fast channel (max speed)	-	1.5	2.5	
				Slow channel (max speed)	-	1.5	2.5	
			Differential	Fast channel (max speed)	-	1	2	
				Slow channel (max speed)	-	1	2	
ENOB	Effective number of bits		Single ended	Fast channel (max speed)	10.4	10.5	-	bits
				Slow channel (max speed)	10.4	10.5	-	
			Differential	Fast channel (max speed)	10.8	10.9	-	
				Slow channel (max speed)	10.8	10.9	-	
SINAD	Signal-to-noise and distortion ratio		Single ended	Fast channel (max speed)	64.4	65	-	dB
				Slow channel (max speed)	64.4	65	-	
			Differential	Fast channel (max speed)	66.8	67.4	-	
				Slow channel (max speed)	66.8	67.4	-	
SNR	Signal-to-noise ratio		Single ended	Fast channel (max speed)	65	66	-	
				Slow channel (max speed)	65	66	-	
			Differential	Fast channel (max speed)	67	68	-	
				Slow channel (max speed)	67	68	-	

Table 70. ADC accuracy - limited test conditions 2(1)(2)(3)

Sym-bol	Parameter	Conditions(4)			Min	Typ	Max	Unit
ET	Total unadjusted error	ADC clock frequency ≤ 80 MHz, Sampling rate ≤ 5.33 Msps, 2 V ≤ V_{DDA}	Single ended	Fast channel (max speed)	-	4	6.5	LSB
				Slow channel (max speed)	-	4	6.5	
			Differential	Fast channel (max speed)	-	3.5	5.5	
				Slow channel (max speed)	-	3.5	5.5	
EO	Offset error		Single ended	Fast channel (max speed)	-	1	4.5	
				Slow channel (max speed)	-	1	5	
			Differential	Fast channel (max speed)	-	1.5	3	
				Slow channel (max speed)	-	1.5	3	
EG	Gain error		Single ended	Fast channel (max speed)	-	2.5	6	
				Slow channel (max speed)	-	2.5	6	
			Differential	Fast channel (max speed)	-	2.5	3.5	
				Slow channel (max speed)	-	2.5	3.5	
ED	Differential linearity error		Single ended	Fast channel (max speed)	-	1	1.5	
				Slow channel (max speed)	-	1	1.5	
			Differential	Fast channel (max speed)	-	1	1.2	
				Slow channel (max speed)	-	1	1.2	
EL	Integral linearity error		Single ended	Fast channel (max speed)	-	1.5	3.5	
				Slow channel (max speed)	-	1.5	3.5	
			Differential	Fast channel (max speed)	-	1	3	
				Slow channel (max speed)	-	1	2.5	
ENOB	Effective number of bits		Single ended	Fast channel (max speed)	10	10.5	-	bits
				Slow channel (max speed)	10	10.5	-	
			Differential	Fast channel (max speed)	10.7	10.9	-	
				Slow channel (max speed)	10.7	10.9	-	
SINAD	Signal-to-noise and distortion ratio		Single ended	Fast channel (max speed)	62	65	-	dB
				Slow channel (max speed)	62	65	-	
			Differential	Fast channel (max speed)	66	67.4	-	
				Slow channel (max speed)	66	67.4	-	
SNR	Signal-to-noise ratio		Single ended	Fast channel (max speed)	64	66	-	
				Slow channel (max speed)	64	66	-	
			Differential	Fast channel (max speed)	66.5	68	-	
				Slow channel (max speed)	66.5	68	-	

Figure 29. Typical connection diagram using the ADC



1. Refer to *Table 67: ADC characteristics* for the values of R_{AIN} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (refer to *Table 61: I/O static characteristics* for the value of the pad capacitance). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.
3. Refer to *Table 61: I/O static characteristics* for the values of Ilkg.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 15: Power supply scheme*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

Table 76. COMP characteristics(1) (continued)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{DDA}(COMP)	Comparator consumption from V_{DDA}	Ultra-low-power mode	Static	-	400	600	nA
			With 50 kHz ±100 mV overdrive square signal	-	1200	-	
		Medium mode	Static	-	5	7	µA
			With 50 kHz ±100 mV overdrive square signal	-	6	-	
		High-speed mode	Static	-	70	100	
			With 50 kHz ±100 mV overdrive square signal	-	75	-	
I_{bias}	Comparator input bias current	-		-	-	-(4)	nA

1. Guaranteed by design, unless otherwise specified.
2. Refer to *Table 26: Embedded internal voltage reference*.
3. Guaranteed by characterization results.
4. Mostly I/O leakage when used in analog mode. Refer to I_{lkg} parameter in *Table 61: I/O static characteristics*.

6.3.22 Operational amplifiers characteristics

Table 77. OPAMP characteristics(1)

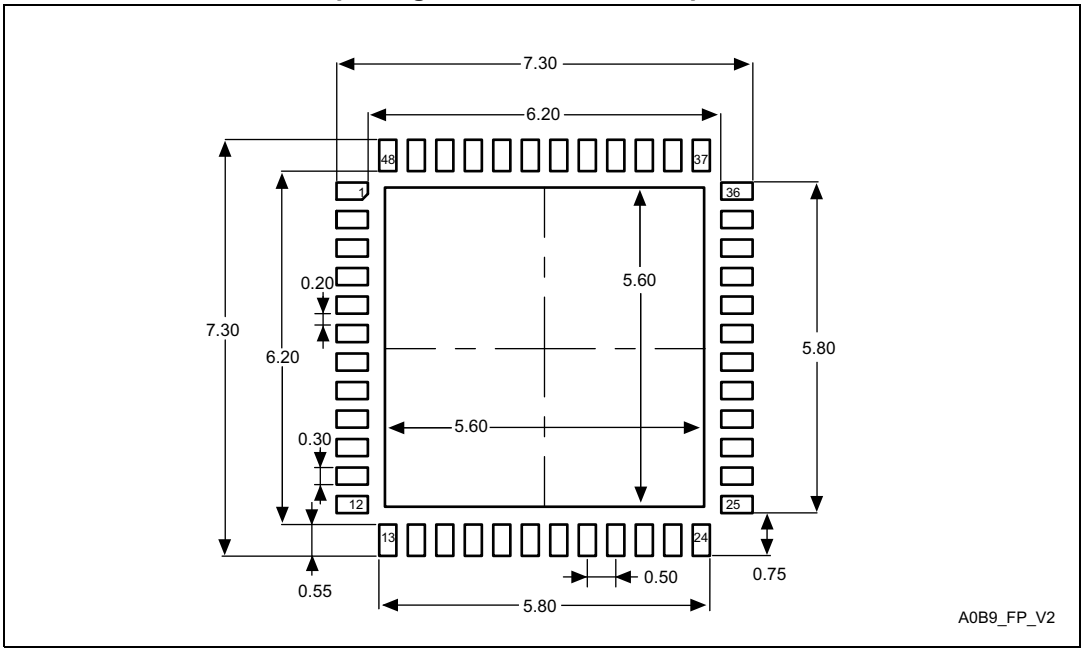
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage(2)	-	1.8	-	3.6	V
CMIR	Common mode input range	-	0	-	V_{DDA}	V
VI_{OFFSET}	Input offset voltage	25 °C, No Load on output.	-	-	±1.5	mV
		All voltage/Temp.	-	-	±3	
ΔVI_{OFFSET}	Input offset voltage drift	Normal mode	-	±5	-	µV/°C
		Low-power mode	-	±10	-	
TRIMOFFSETP TRIMLPOFFSETP	Offset trim step at low common input voltage (0.1 x V_{DDA})	-	-	0.8	1.1	mV
TRIMOFFSETN TRIMLPOFFSETN	Offset trim step at high common input voltage (0.9 x V_{DDA})	-	-	1	1.35	

Table 99. UFQFPN48 - 48-lead, 7x7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
D	6.900	7.000	7.100	0.2717	0.2756	0.2795
E	6.900	7.000	7.100	0.2717	0.2756	0.2795
D2	5.500	5.600	5.700	0.2165	0.2205	0.2244
E2	5.500	5.600	5.700	0.2165	0.2205	0.2244
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
T	-	0.152	-	-	0.0060	-
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
e	-	0.500	-	-	0.0197	-
ddd	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 56. UFQFPN48 - 48-lead, 7x7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.